

# Jaidah Mohan

## List of Publications by Year in descending order

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23  
papers

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759233

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752698

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#	ARTICLE	IF	CITATIONS
1	Ferroelectric Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> Thin Films: A Review of Recent Advances. <i>Jom</i> , 2019, 71, 246-255.	1.9	217
2	Large ferroelectric polarization of TiN/Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> /TiN capacitors due to stress-induced crystallization at low thermal budget. <i>Applied Physics Letters</i> , 2017, 111, .	3.3	201
3	Effect of film thickness on the ferroelectric and dielectric properties of low-temperature (400°C) Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> films. <i>Applied Physics Letters</i> , 2018, 112, .	3.3	111
4	Low-voltage operation and high endurance of 5-nm ferroelectric Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> capacitors. <i>Applied Physics Letters</i> , 2018, 113, .	3.3	50
5	A Comprehensive Study on the Effect of TiN Top and Bottom Electrodes on Atomic Layer Deposited Ferroelectric Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> Thin Films. <i>Materials</i> , 2020, 13, 2968.	2.9	30
6	Stress-Induced Crystallization of Thin Hf <sub>1-x</sub> Zr <sub>x</sub> O <sub>2</sub> Films: The Origin of Enhanced Energy Density with Minimized Energy Loss for Lead-Free Electrostatic Energy Storage Applications. <i>ACS Applied Materials &amp; Interfaces</i> , 2019, 11, 5208-5214.	8.0	28
7	Low-Thermal-Budget Fluorite-Structure Ferroelectrics for Future Electronic Device Applications. <i>Physica Status Solidi - Rapid Research Letters</i> , 2021, 15, 2100028.	2.4	24
8	Atomic Layer Deposition of Layered Boron Nitride for Large-Area 2D Electronics. <i>ACS Applied Materials &amp; Interfaces</i> , 2020, 12, 36688-36694.	8.0	22
9	Effect of hydrogen derived from oxygen source on low-temperature ferroelectric TiN/Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> /TiN capacitors. <i>Applied Physics Letters</i> , 2019, 115, .	3.3	21
10	Ferroelectric polarization retention with scaling of Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> on silicon. <i>Applied Physics Letters</i> , 2021, 118, .	3.3	19
11	Improvement in ferroelectricity and breakdown voltage of over 20-nm-thick Hf <sub>x</sub> Zr <sub>1-x</sub> O <sub>2</sub> /ZrO <sub>2</sub> bilayer by atomic layer deposition. <i>Applied Physics Letters</i> , 2020, 117, .	3.3	17
12	Low-thermal-budget (300°C) ferroelectric TiN/Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> /TiN capacitors realized using high-pressure annealing. <i>Applied Physics Letters</i> , 2021, 119, .	3.3	16
13	Ferroelectric TiN/Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> /TiN Capacitors with Low-Voltage Operation and High Reliability for Next-Generation FRAM Applications. , 2018, , .		15
14	Low Temperature Thermal Atomic Layer Deposition of Aluminum Nitride Using Hydrazine as the Nitrogen Source. <i>Materials</i> , 2020, 13, 3387.	2.9	12
15	Correlation between ferroelectricity and ferroelectric orthorhombic phase of Hf <sub>x</sub> Zr <sub>1-x</sub> O <sub>2</sub> thin films using synchrotron x-ray analysis. <i>APL Materials</i> , 2021, 9, .	5.1	9
16	Improvement of Ferroelectricity and Fatigue Property of Thicker Hf <sub>x</sub> Zr <sub>1-x</sub> O <sub>2</sub> /ZrO <sub>2</sub> Bi-layer. <i>ECS Transactions</i> , 2020, 98, 63-70.	0.5	9
17	Extremely Low Leakage Threshold Switch with Enhanced Characteristics via Ag Doping on Polycrystalline ZnO Fabricated by Facile Electrochemical Deposition for an X-Point Selector. <i>ACS Applied Electronic Materials</i> , 2021, 3, 2309-2316.	4.3	8
18	Low Temperature (400°C) Ferroelectric Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> Capacitors for Next-Generation FRAM Applications. , 2017, , .		6

#	ARTICLE	IF	CITATIONS
19	A Novel Combinatorial Approach to the Ferroelectric Properties in Hf x Zr 1â” x O 2 Deposited by Atomic Layer Deposition. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100053.	2.4	3
20	Relaxation Induced by Imprint Phenomena in Low-Temperature (400 Å°C) Processed Hf<sub>0.5</sub>Zr<sub>0.5</sub>O<sub>2</sub>-Based Metal-Ferroelectric-Metal Capacitors. ACS Applied Electronic Materials, 2022, 4, 1405-1414.	4.3	2
21	Lowâ€Thermalâ€Budget Fluoriteâ€Structure Ferroelectrics for Future Electronic Device Applications. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2170020.	2.4	1
22	Highly Reliable Selection Behavior With Controlled Ag Doping of Nano-Polycrystalline ZnO Layer for 3D X-Point Framework. IEEE Electron Device Letters, 2022, 43, 21-24.	3.9	1
23	Nano-polycrystalline Ag-doped ZnO layer for steep-slope threshold switching selectors. AIP Advances, 2021, 11, 115213.	1.3	0